



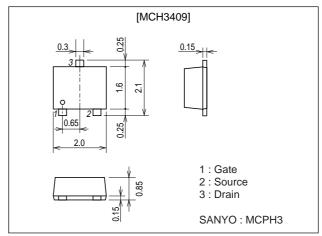
Ultrahigh-Speed Switching Applications

Features

- · Low ON-resistance.
- · Ultrahigh-speed switching.
- 2.5V drive.

Package Dimensions

unit : mm 2167



Specifications

Absolute Maximum Ratings at Ta=25°C

| Parameter | Symbol | Conditions | Ratings | Unit |
|-----------------------------|--------|--|-------------|------|
| Drain-to-Source Voltage | VDSS | | 20 | V |
| Gate-to-Source Voltage | VGSS | | ±10 | V |
| Drain Current (DC) | ID | | 2.0 | Α |
| Drain Current (Pulse) | IDP | PW≤10μs, duty cycle≤1% | 8.0 | Α |
| Allowable Power Dissipation | PD | Mounted on a ceramic board (900mm ² X0.8mm) | 0.9 | W |
| Channel Temperature | Tch | | 150 | °C |
| Storage Temperature | Tstg | | -55 to +150 | °C |

Electrical Characteristics at Ta=25°C

| Parameter | Symbol | Conditions | Ratings | | | Unit |
|--|-----------------------|---|---------|-----|-----|-------|
| | | | min | typ | max | Offic |
| Drain-to-Source Breakdown Voltage | V(BR)DSS | I _D =1mA, V _{GS} =0 | 20 | | | V |
| Zero-Gate Voltage Drain Current | IDSS | V _{DS} =20V, V _{GS} =0 | | | 1 | μΑ |
| Gate-to-Source Leakage Current | IGSS | V _{GS} =±8V, V _{DS} =0 | | | ±10 | μΑ |
| Cutoff Voltage | VGS(off) | V _{DS} =10V, I _D =1mA | 0.4 | | 1.3 | V |
| Forward Transfer Admittance | yfs | V _{DS} =10V, I _D =1A | 2.4 | 3.5 | | S |
| Static Drain-to-Source On-State Resistance | R _{DS} (on)1 | I _D =1A, V _{GS} =4V | | 100 | 130 | mΩ |
| | R _{DS} (on)2 | I _D =0.5A, V _G S=2.5V | | 130 | 180 | mΩ |

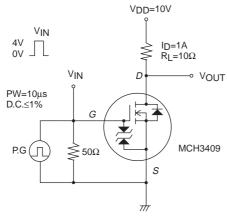
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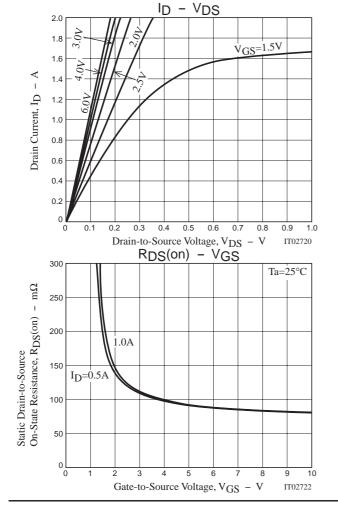
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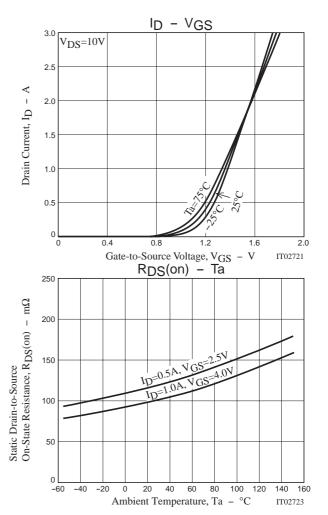
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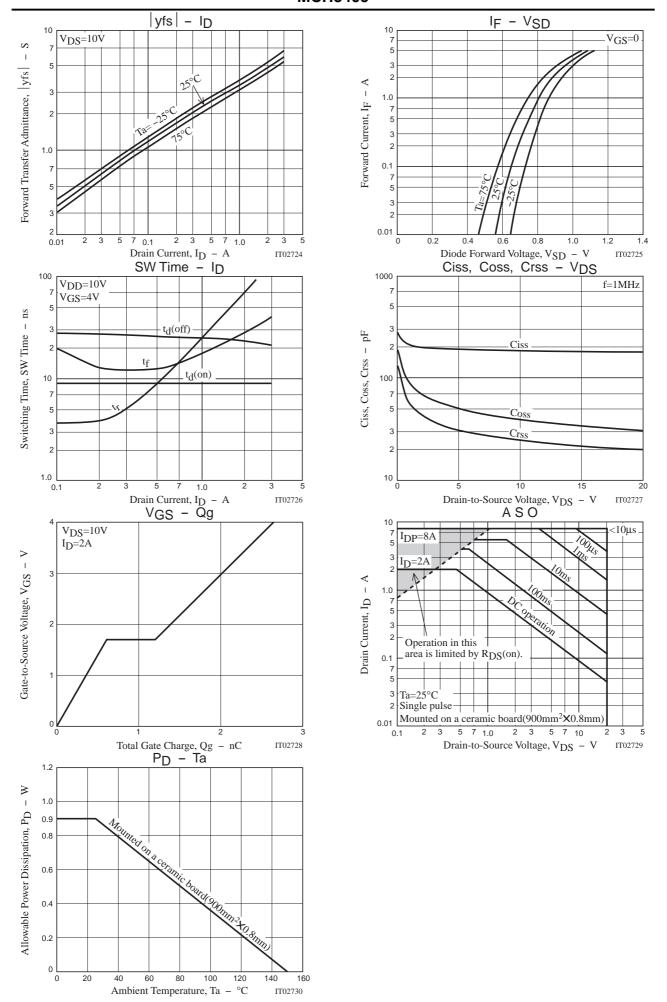
| Parameter | Symbol | Conditions | Ratings | | | Unit |
|-------------------------------|----------------------|---|---------|------|-----|------|
| | Symbol | | min | typ | max | Unit |
| Input Capacitance | Ciss | V _{DS} =10V, f=1MHz | | 190 | | pF |
| Output Capacitance | Coss | V _{DS} =10V, f=1MHz | | 40 | | pF |
| Reverse Transfer Capacitance | Crss | VDS=10V, f=1MHz | | 25 | | pF |
| Turn-ON Delay Time | t _d (on) | See specified Test Circuit | | 9 | | ns |
| Rise Time | t _r | See specified Test Circuit | | 25 | | ns |
| Turn-OFF Delay Time | t _d (off) | See specified Test Circuit | | 25 | | ns |
| Fall Time | tf | See specified Test Circuit | | 18 | | ns |
| Total Gate Charge | Qg | V _{DS} =10V, V _{GS} =4V, I _D =2.0A | | 2.7 | | nC |
| Gate-to-Source Charge | Qgs | V _{DS} =10V, V _{GS} =4V, I _D =2.0A | | 0.6 | | nC |
| Gate-to-Drain "Miller" Charge | Qgd | V _{DS} =10V, V _{GS} =4V, I _D =2.0A | | 0.6 | | nC |
| Diode Forward Voltage | V _{SD} | I _S =2.0A, V _{GS} =0 | | 0.87 | 1.2 | V |

Switching Time Test Circuit









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